

isc N-Channel Mosfet Transistor

IRF530FI

• FEATURES

- Low $R_{DS(on)}$
- V_{GS} Rated at $\pm 20V$
- Silicon Gate for Fast Switching Speed
- Rugged
- Low Drive Requirements

• DESCRIPTION

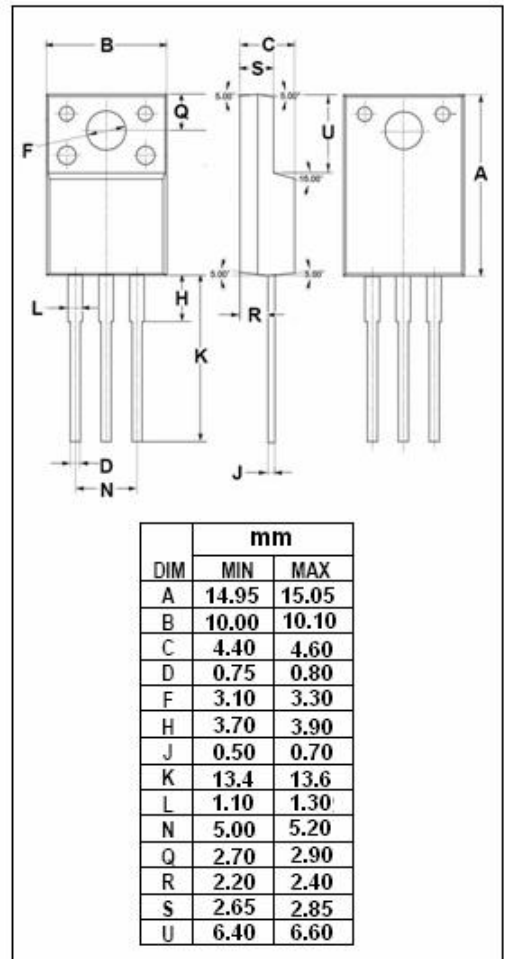
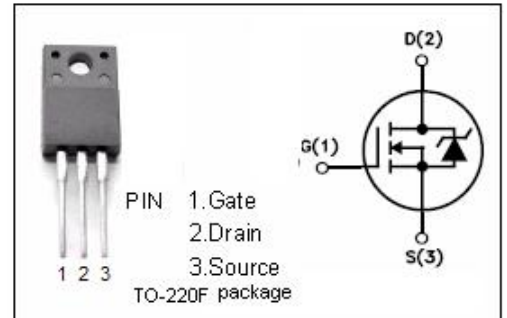
- Designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.

• ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	10	A
I_{DM}	Drain Current-Single Plused	40	A
P_D	Total Dissipation @ $T_C=25^\circ C$	40	W
T_j	Max. Operating Junction Temperature	-55~175	$^\circ C$
T_{stg}	Storage Temperature	-55~175	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.9	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	80	$^\circ C/W$



isc N-Channel Mosfet Transistor**IRF530FI****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=0.25\text{mA}$	100			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25\text{mA}$	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=8\text{A}$			0.16	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			± 500	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100\text{V}; V_{GS}=0$			250	μA
V_{SD}	Forward On-Voltage	$I_S=10\text{A}; V_{GS}=0$			2.5	V